

Ceramics International 29 (2003) 893-896



www.elsevier.com/locate/ceramint

Thermal conductivity of AlN ceramics sintered with CaF₂ and YF₃

Liang Qiao^{a,*}, Heping Zhou^a, Renli Fu^b

^aState Key Laboratory of New Ceramics and Fine Processing, Department of Materials Science and Engineering, Tsinghua University, Beijing 100084, PR China

^bCollege of Mechanical-Electronic and Material Engineering, China University of Mining and Technology, Jiangsu, Xuzhou 221008, PR China

Received 4 July 2002; received in revised form 16 November 2002; accepted 5 December 2002

Abstract

Dense AlN ceramics with a thermal conductivity of $180 \text{W/m} \cdot \text{K}$ were obtained at the sintering temperature of $1750 \,^{\circ}\text{C}$ using CaF_2 and YF_3 as additives. At temperatures below $1650 \,^{\circ}\text{C}$, the shrinkage of AlN ceramics is promoted by liquid $(\text{Ca}, \text{Y})\text{F}_2$ and $\text{Ca}_{12}\text{Al}_{14}\text{O}_{32}\text{F}_2$. Liquid $\text{Ca}_{\text{Y}}\text{AlO}_4$ mainly improves the densification of the sample when the sintering temperature increases to $1750 \,^{\circ}\text{C}$. The formation of liquid $(\text{Ca}, \text{Y})\text{F}_2$ at a relatively low temperature results in homogeneous YF_3 distribution around the AlN particles, which benefits the removal of oxygen impurity in the AlN lattice, and thus a higher thermal conductivity. © 2003 Elsevier Ltd and Techna S.r.l. All rights reserved.

Keywords: A. Sintering; B. Microstructure-final; C. Thermal conductivity; Aluminum nitride

1. Introduction

Aluminum nitride is a promising substrate and package material for high power integrated circuits because of its high thermal conductivity, low dielectric constant and thermal expansion coefficient close to that of silicon and high electrical resistivity [1,2]. However, AlN is difficult to sinter due to its high covalent bonding. For full densification, rare-earth and/or alkaline earth oxides are often added as sintering aids in the fabrication of AlN ceramics [3,4]. These sintering aids play a double role during the sintering. One is to form a liquid phase that promotes densification by liquid-phase sintering. The other is to improve the thermal conductivity by reducing the oxygen impurities in the AlN lattice. Hundere et al. [5] studied the chemical reactions when sintering AlN ceramics with YF₃ additions. Liu et al. [6] achieved AlN ceramics with a thermal conductivity above 170 W/m·K using CaF₂ and YF₃ as additives. However, the effect of YF₃ on the thermal conductivity was not clear from their study. In this paper, CaF₂, YF₃ and Y₂O₃ were used as sintering aids to explore the effect of YF₃ on the thermal conductivity of AlN ceramics.

E-mail address: qiaoliang98@mails.tsinghua.edu.cn (L. Qiao).

2. Experimental procedure

The commercial AlN powder (H type, Tokuyama, Japan) used in this study has an oxygen impurity content of 0.9 wt.% and a specific surface area of 2.7 m²g⁻¹. AlN powder was mixed with CaF₂, YF₃ and Y₂O₃ (analytical reagents) and ball-milled by planetary milling for 2 h using ethanol as a mixing medium. The dried powder was mixed with polyvinyl butyral (PVB) binder before uniaxially pressing the powder into pellets 10 mm in diameter and 5 mm thick. The pellets were de-waxed at 550 °C and then placed into a BN crucible and sintered at 1350, 1500, 1650 and 1750 °C for different times in a graphite furnace with a flowing nitrogen atmosphere. The compositions of the specimens are shown in Table 1.

Shrinkage of the sintered pellets was measured with a vernier caliper. Densities of samples CYFA and CYOA sintered at 1750 °C for 4 h were measured by Archimedes displacement method with distilled water as the immersion medium. Using XRD with CuK_{α} radiation, the secondary phases in AlN specimens after sintering were identified. Microstructure of fracture surfaces was observed by scanning electron microscopy (SEM, OPTON, CSM950). The thermal conductivity at room temperature was measured by a laser flash technique. To determine the lattice parameters, the samples sintered at 1750 °C for 4 h were scanned from 90° to 140 at the rate of 0.1 °/min using XRD with CuK_{α} radiation.

^{*} Corresponding author: Tel.: +86-10-62772550; fax: +86-10-62772549.

Table 1 Compositions of different samples in the experiments

Sample	(wt.%)			
	CaF ₂	YF_3	Y_2O_3	AlN
YFA	0	3	0	97
CYFA	4	3	0	93
CYOA	4	0	2	94

3. Results

Table 2 shows that the secondary phases in samples YFA and CYFA after sintering at different temperatures for 0.5 h. The chemical composition of the secondary phases in YFA samples changes in the order YOF \rightarrow Y₃Al₅O₁₂ (YAG) \rightarrow Y₄Al₂O₉ (YAM) \rightarrow YN when the firing temperature increases from 1350 to 1650 °C. This is similar to the results achieved by Hundere et al. [5] However, it seems impossible that Y₂O₃ can be formed as an intermediate product from the reaction between YF₃ and Al₂O₃ as Hundere et al. [5] presumed since no Y₂O₃ is found with the formation of yttrium aluminates before 1500 °C in Sample YFA. YF₃ is supposed to react with Al₂O₃ and form YOF (Tetragonal) and AlF₃ as follows:

$$3YF_3(1) + Al_2O_3(s) = 3YOF(s) + 2AlF_3(g)$$
 (1)

In sample CYFA, $(Ca,Y)F_2$ and $Ca_{12}Al_{14}O_{32}F_2$ form at 1350 °C. Considering the greater shrinkages of Sample CYFA fired below 1650 °C compared with that of sample YFA, the formation of liquid $(Ca,Y)F_2$ and calcium aluminates promotes densification of sample CYFA at temperatures lower than 1650 °C. With increasing temperature, YF₃ is presumably released from $(Ca,Y)F_2$ and reacts with Al_2O_3 to form YAP and YAM, which are detected at 1500 °C as shown in Table 2. After heating at 1650 °C, the yttrium aluminates change into Y_2O_3 under the nitrogen ambient in a graphite furnace.

Samples CYFA and CYOA sintered at 1750 °C for 4 h reach full densification with similar densities of 3.28 g/cm³. However, the thermal conductivity of sample CYFA is 180 W/mK, which is much higher than the 152

Table 2 Secondary phases in samples YFA and CYFA after sintering at different temperatures for $0.5\ h$

Sintering temperature (°C)	Sample		
temperature (C)	YFA	CYFA	
1350	YOF	(Ca,Y)F ₂ , Ca _{1 2} Al ₁₄ O ₃₂ F ₂	
1500	$Y_3Al_5O_{12}$	CaF ₂ , YOF, Ca ₁₂ Al ₁₄ O ₃₂ F ₂ , YAlO ₃ , Y ₄ Al ₂ O ₉	
1650	$Y_4Al_2O_9,YN$	Y_2O_3	

W/m·K of sample CYOA. The X-ray patterns in samples CYFA and CYOA sintered at 1750 °C for 4 h are shown in Fig. 1. It can be seen from this figure the similar phase compositions containing YAM, CaYAlO₄ and Y₂O₃ in the two samples. Considering their similar densities, liquid CaYAlO₄ promotes densification of sample CYFA at 1750 °C [7,8].

Fig. 2 shows the morphology of fracture surfaces of sample CYFA and CYOA sintered at 1750 °C for 4 h. As shown in this figure, the grains in the two samples have a close contact between them, which agrees with the high densification of the sintered bodies. However, the polyhedral grains in sample CYFA grow homogeneous, which is different than the irregular grain shape in sample CYOA. The addition of YF₃ obviously improves the grain growth in the sintering regardless of the slight effect on the densification compared with adding Y₂O₃.

4. Discussion

In general, densification, grain boundary phases and oxygen content in the AlN lattice play an important role on the thermal conductivity of AlN ceramics. Since both sample CYFA and sample CYOA reach the density at 1750 °C, densification is not the main reason for the different thermal conductivities of the two samples.

Kurokawa et al. [9] published the relationship between thermal conductivity and oxygen concentration for a series of AlN ceramic samples, which were prepared with a sintering additive containing Ca. The measured oxygen content of the sintered body strongly reflects the oxygen content in the AlN lattice since all the second phases produced from this sintering aid vaporized during sintering. The thermal conductivity is

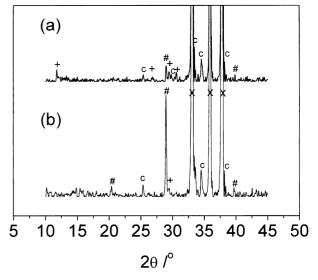
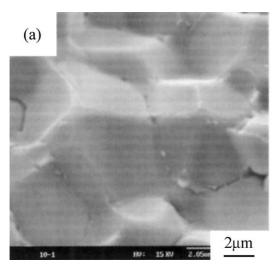


Fig. 1. X-ray patterns of samples CYFA (a) and CYOA (b); $(+YAM, \times AlN, \# Y_2O_3, c \ CaYAlO_4)$.



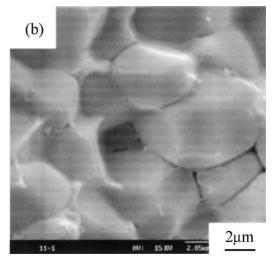


Fig. 2. Morphology on the fracture surface of different samples sintered at 1750 °C for 4 h; (a) CYFA and (b) CYOA.

mainly controlled by the oxygen content in the AlN lattice when there are no grain boundary phases. Thus, the effect of grain boundary phases on the thermal conductivity can be indirectly shown by measuring AlN cell volume and oxygen content in the AlN lattice of sintered bodies. The measurement of the unit cell volume of samples CYFA and CYOA sintered at 1750 °C for 4 h shows that the cell volume of sample CYFA is 41.760 ų, greater than that of sample CYOA, which is 41.753 ų. According to the relations between the thermal conductivity and AlN cell volume, as shown in Fig. 3, it can be seen that the thermal conductivities of samples CYFA and CYOA have a good agreement with the polynomial fit curve. This implies that the grain boundary phases have no prominent effect on the thermal conductivity.

Oxygen, covering the surface of AlN powder, diffuses into the AlN lattice to form oxygen-related defects at temperatures between 1400 and 1800 °C during the sintering of AlN ceramics [10]. At low oxygen level, the AlN

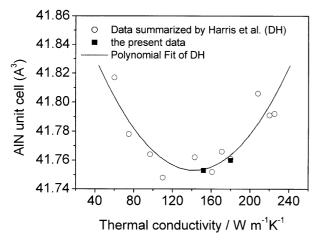


Fig. 3. AlN unit cell volume, as determined by X-ray diffraction measurements, as a function of thermal conductivity. The curve is polynomial fit of data published by Kurokawa et al. [9].

cell volume decreases with increasing oxygen concentration due to the formation of Al vacancies. However, a higher oxygen concentration also produces a larger cell volume at the high oxygen content side of the transition, as Harris et al. summarized [11]. From the normalized change in AlN unit cell volume as a function of oxygen concentration [11], the oxygen concentrations of samples CYFA and CYOA are calculated to be 0.78 and 0.9 at.%, respectively. Thus, it is obvious that the higher thermal conductivity of sample CYFA is attributed to the lower oxygen concentration compared with sample CYOA.

Here a possible mechanism is proposed to explore the reason why sample CYFA has a lower oxygen concentration from the phase change in the firing. During sintering of AlN ceramics with Y₂O₃ addition, the complete reaction between Y2O3 and the oxygen on the AlN particles is necessary to decrease the final oxygen concentration in AlN lattice [12]. Using concurrent addition of CaF₂ and Y₂O₃, oxygen is difficult to completely react with Y₂O₃ to form the stable yttrium aluminates before 1650 °C due to the solid phase reaction between Y₂O₃ and Al₂O₃ and the inhomogeneous liquid distribution, which makes oxygen have chances to enter AlN lattice to form oxygen-related defects and decrease the thermal conductivity of AlN ceramics [8]. However, in CaF₂-YF₃ system, phase (Ca,Y)F₂ occurs at a relatively low temperature of 1350 °C and becomes liquid above 1400 °C according to the phase diagram [13]. The flow and redistribution of liquid (Ca,Y)F₂ make YF₃ have sufficient chances to contact oxygen on AlN surface and react with it, which can limit the diffusion of oxygen from the surface of AlN particles to AlN lattice at temperatures above 1400 °C. As shown in Fig. 1, the remaining Y₂O₃ in Sample CYFA sintered at 1750 °C for 4 h also implies a complete oxygen elimination of AlN particles since all the oxygen in the second phases comes from the surface of the original AlN particles. Furthermore, YAM phase, in which oxygen has low activity [12], forms easily during sintering of CYFA samples due to no additional oxygen in CaF₂ and YF₃. This benefits the removal of oxygen from the AlN lattice at 1750 °C. Thus, the oxygen concentration in the AlN lattice is lower in sample CYFA compared with that in sample CYOA.

5. Conclusions

Using CaF₂ and YF₃, dense AlN ceramics was achieved with a thermal conductivity of 180 W/m·K. The occurrence of liquid (Ca,Y)F₂ and Ca₁₂Al₁₄O₃₂F₂ is the main reason for the densification of AlN ceramics before 1650 °C. While, the densification is promoted by the action of liquid CaYAlO₄ at 1750 °C. Compared with the sample added with CaF₂ and Y₂O₃, grain boundary phases have no prominent effect on the thermal conductivity of AlN ceramics with CaF₂ and YF₃ addition. Oxygen concentration in the AlN lattice is the main controlling factor for the difference in the thermal conductivities of dense AlN ceramics. The concurrent addition of CaF₂ and YF₃ decreases the oxygen concentration in the AIN lattice of the sintered samples due to the formation of liquid (Ca,Y)F₂ at a relatively low temperature, and thus benefits achieving a high thermal conductivity.

Acknowledgements

This work was supported by Guangdong Research and Development Center for New Functional Ceramic Materials.

References

- G.A. Slack, Nonmetallic crystals with high thermal conductivity, J. Phys. Chem. Solids 34 (1973) 321–335.
- [2] L.M. Sheppard, Aluminum nitride: a versatile but challenging material, Am. Ceram. Bull. 69 (11) (1990) 1801–1803.
- [3] K. Komeya, H. Inoue, A. Tsuge, Role of Y₂O₃ and SiO₂ additions in sintering of AlN, J. Am. Ceram. Soc. 54 (1974) 411–412.
- [4] K. Komeya, A. Tsuge, A. Inoue, Effect of CaCO₃ addition on the sintering of AlN, J. Mater. Sci. Lett. 1 (1986) 325–326.
- [5] A.M. Hundere, M.A. Einarsrud, Effects of reduction of the Al-Y-O containing secondary phases during sintering of AlN with YF₃ additions, J Eur. Ceram. Soc. 16 (1996) 899–906.
- [6] Y. Liu, H. Zhou, L. Qiao, Y. Wu, Low-temperature sintering of aluminum nitride with YF₃-CaF₂ binary additive, J. Mater. Sci. Lett. 18 (1999) 703–704.
- [7] J. Jarrige, K. Bouzouita, C. Doradoux, M. Billy, A new method for fabrication of dense aluminium nitride bodies at a temperature as low as 1600 °C, J. Eur. Ceram. Soc. 12 (1993) 279–285.
- [8] L. Qiao, H. Zhou, H. Xue, S. Wang, Effect of Y₂O₃ on low temperature sintering and thermal conductivity of AlN ceramics, J. Eur. Ceram. Soc. 23 (2003) 61–67.
- [9] Y. Kurokawa, K. Utsumi, H. Takamizawa, Development and microstructural characterization of high-thermal-conductivity aluminum nitride ceramics, J. Am. Ceram. Soc. 71 (1988) 588–594.
- [10] K. Watari, M.E. Brito, M. Yasuoka, M.C. Valecillos, S. Kanzaki, Influence of powder characteristics on sintering process and thermal-conductivity of aluminum nitride ceramics, J. Ceram. Soc. Jpn. 103 (1995) 891–900.
- [11] J.H. Harris, R.A. Youngman, R.G. Teller, On the nature of the oxygen-related defect in aluminum nitride, J. Mater. Res. 5 (8) (1990) 1763–1773.
- [12] T.B. Jackson, A.V. Virkar, K.L. More, R.B. Dinwiddie, R.A. Cutler, High-thermal-conductivity aluminum nitride ceramics: the effect of thermodynamic, kinetic, and microstructural factors, J. Am. Ceram. Soc. 80 (6) (1997) 1421–1435.
- [13] R.S. Roth, T. Negas, L.P. Cook, Phase Diagrams for Ceramists (V), Acers, Columbus, 1983.